

SiNx Films, Grown using Unaxis ICP Tool, as well as PECVD Tool, Characterizations			
	100 °C (ICP)	250 °C (ICP)	250 °C (PECVD)
Refractive Index	~2	~2	~2
Deposition Rate (nm/min)	17	15.9	~10
Buffered HF Etch Rate (nm/min)	51	51	36
Stress (~200-nm Film on a Si Wafer) (MPa)	-115	-169	260